L Number	Hits	Search Text	DB	Time stamp
-	26032	(pr photoresist photo?resist polymer$3) same mask same (pattern aperture)	USPAT; US-PGPUB	2004/04/17 18:23
-	2	((pr photoresist photo?resist polymer$3) same mask same (pattern aperture)) and (stretch$3 with mask with align$3 with substrate)	USPAT; US-PGPUB	2004/04/17 17:55
-	2	stretch$3 with mask with align$3 with substrate	USPAT; US-PGPUB	2004/04/17 17:56
-	20	stretch$3 same mask same align$3 same substrate	USPAT; US-PGPUB	2004/07/15 11:22
-	8	stretch$3 same mask same align$3 same substrate	EPO; JPO; DERWENT; IBM_TDB	2004/04/17 18:07
-	3	reposition$6 near35 polymer$3 near5 mask	USPAT; US-PGPUB	2004/07/14 17:44
-	8095	(TFT and (resist pr photoresist))	USPAT; US-PGPUB	2004/07/14 17:45
-	6584	((TFT and (resist pr photoresist))) and mask	USPAT; US-PGPUB	2004/07/14 17:45
-	1919	(((TFT and (resist pr photoresist))) and mask) and aperture	USPAT; US-PGPUB	2004/07/15 15:09
-	21	stretch$3 same mask same align$3 same substrate	USPAT; US-PGPUB	2004/07/15 11:25
-	10520	deposit$3 near20 using near20 mask$3	USPAT; US-PGPUB	2004/07/15 13:14
-	1246	(deposit$3 near20 using near20 mask$3) and (TFT (thin near3 film near3 transistor))	USPAT; US-PGPUB	2004/07/15 13:16
-	196	deposit$3 near50 using near50 polymer$3 near50 mask$3	USPAT; US-PGPUB	2004/07/15 13:15
-	18	(deposit$3 near50 using near50 polymer$3 near50 mask$3) and (TFT (thin near3 film near3 transistor))	USPAT; US-PGPUB	2004/07/15 13:53
-	2	flexable near3 polymer	USPAT; US-PGPUB	2004/07/15 13:52
-	8501	((polymer organic) near50 mask)	USPAT; US-PGPUB	2004/07/15 13:55
-	1073	(((polymer organic) near50 mask)) and (TFT (thin near3 film near3 transistor))	USPAT; US-PGPUB	2004/07/15 13:55
-	9406	((polymer$3 organic) near50 mask)	USPAT; US-PGPUB	2004/07/15 13:55
-	1115	(((polymer$3 organic) near50 mask)) and (TFT (thin near3 film near3 transistor))	USPAT; US-PGPUB	2004/07/15 13:56
-	27	(((TFT and (resist pr photoresist))) and mask) and aperture	EPO; JPO; DERWENT; IBM_TDB	2004/07/15 15:34